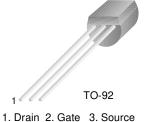


# 2N3819

# **N-Channel RF Amplifier**

- This device is designed for RF amplifier and mixer applications operating up to 450MHz, and for analog switching requiring low capacitance.
- Sourced from process 50.



# **Epitaxial Silicon Transistor**

# **Absolute Maximum Ratings\*** $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DG}$	Drain-Gate Voltage	25	V
$V_{GS}$	Gate-Source Voltage	-25	V
I <sub>D</sub>	Drain Current	50	mA
I <sub>GF</sub>	Forward Gate Current	10	mA
T <sub>STG</sub>	Storage Temperature Range	-55 ~ 150	°C

<sup>\*</sup> This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

# $\textbf{Electrical Characteristics} \ \, \textbf{T}_{\text{C}} = 25 \, ^{\circ} \text{C unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	Off Characteristics					
V <sub>(BR)GSS</sub>	Gate-Source Breakdwon Voltage	$I_G = 1.0 \mu A, V_{DS} = 0$	25			V
I <sub>GSS</sub>	Gate Reverse Current	$V_{GS} = -15V, V_{DS} = 0$			2.0	nA
V <sub>GS</sub> (off)	Gate-Source Cutoff Voltage	$V_{DS} = 15V, I_D = 2.0nA$			8.0	V
V <sub>GS</sub>	Gate-Source Voltage	$V_{DS} = 15V, I_D = 200\mu A$	-0.5		-7.5	V
On Charac	On Characteristics					
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current	$V_{DS} = 15V, V_{GS} = 0$	2.0		20	mA
Small Signal Characteristics						
gfs	Forward Transfer Conductance	$V_{DS} = 15V, V_{GS} = 0, f = 1.0KHz$	2000		6500	μmhos
goss	Output Conductance	$V_{DS} = 15V, V_{GS} = 0, f = 1.0KHz$			50	μmhos
Уfs	Forward Transfer Admittance	$V_{DS} = 15V, V_{GS} = 0, f = 1.0KHz$	1600			μmhos
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15V, V_{GS} = 0, f = 1.0KHz$			8.0	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	$V_{DS} = 15V, V_{GS} = 0, f = 1.0KHz$			4.0	pF

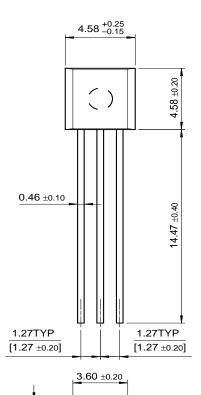
# Thermal Characteristics T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W
* Device mounted on FR-4 PCB 1.5" × 1.6" × 0.06"			

These rating are based on a maximum junction temperature of 150 degrees C.
These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# **Package Dimensions**

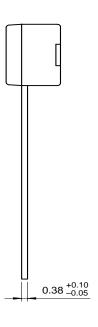
TO-92



(R2.29)

1.02 ±0.10 0.38 <sup>+0.10</sup> 0.38 −0.05





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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS <sup>TM</sup>	SyncFET™
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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	OCXTM	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET®
The Power Franc	hise™	OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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Rev. I1

### **PRODUCT STATUS DEFINITIONS**

### **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.